



STANFORD
nanoHeat

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<http://www.nanoheat.stanford.edu>

Novel Thermal Interface Materials for 3D Chip Stacks

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sril@stanford.edu

Advisor: Prof. Ken Goodson

Department of Mechanical Engineering, Stanford

IEEE SFBA Nanotechnology Council Talk

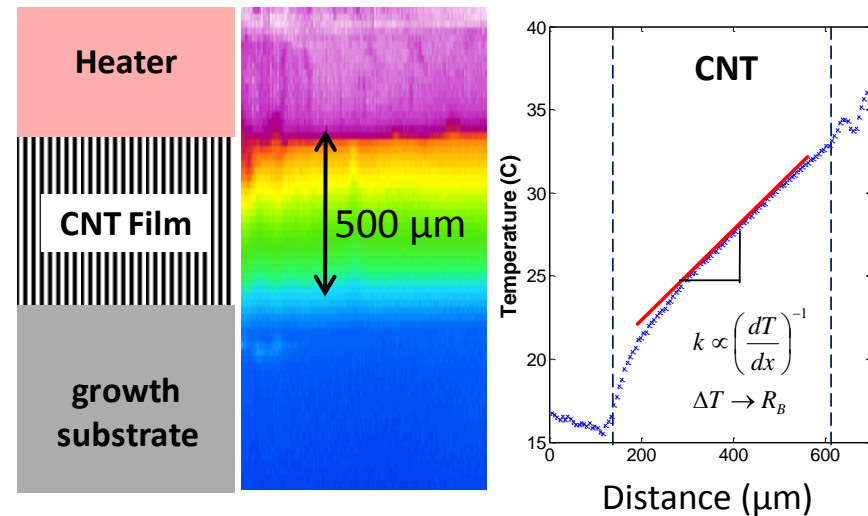
Oct 16, 2012

Outline

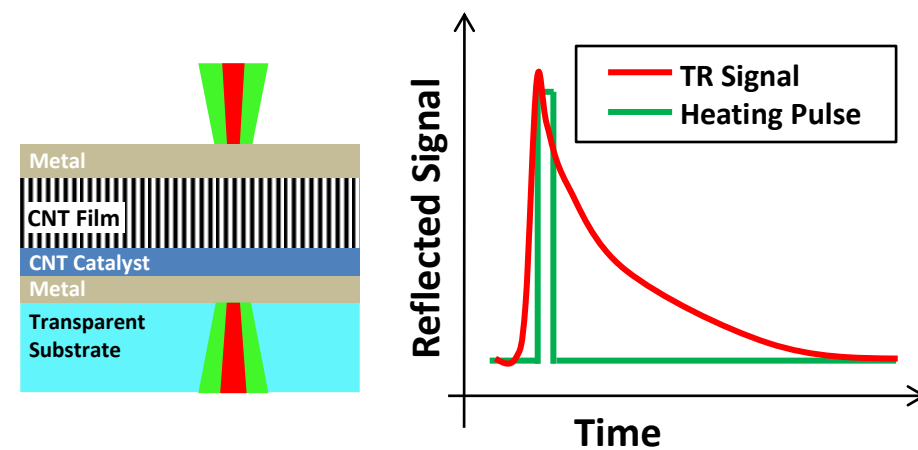
- **Stanford Nano Heat Lab**
 - Overview of Metrology and Materials
- **Materials for Thermal Management**
 - 3D chip attachments and conductive underfills
 - High density aligned CNT composites
 - Aligned CNT nanotape
 - Mechanical Characterization

Thermal and Mechanical Characterization

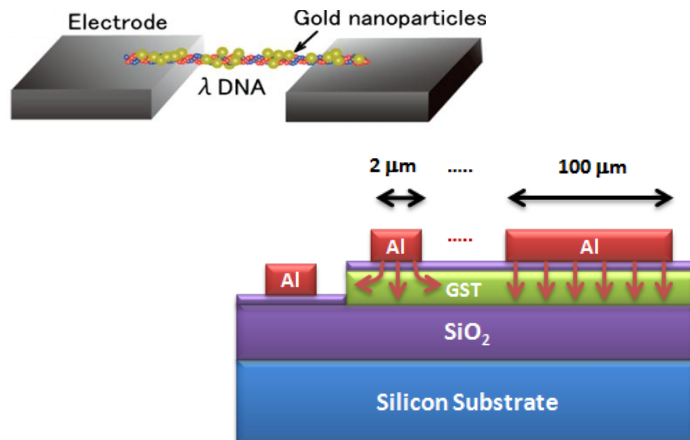
Cross-sectional IR Microscopy



Pico/Nanosecond Thermoreflectance

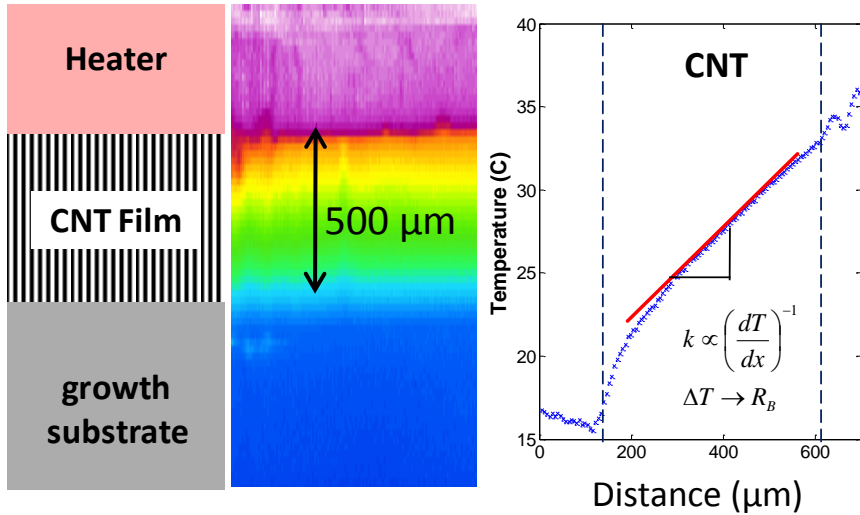


Electrothermal Characterization

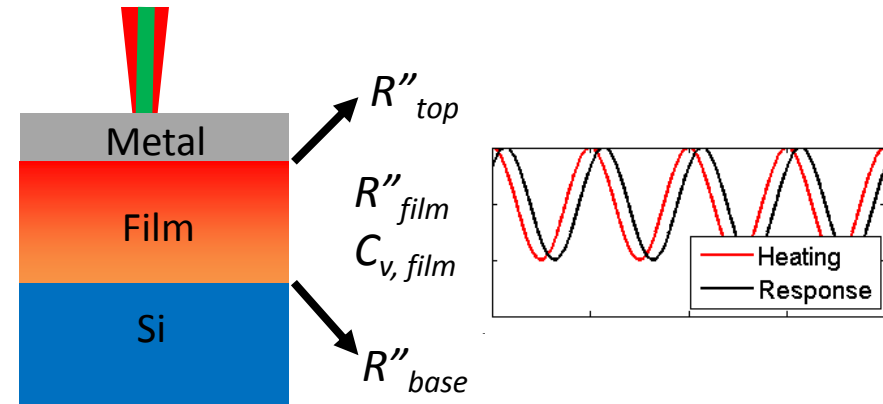


Thermal and Mechanical Characterization

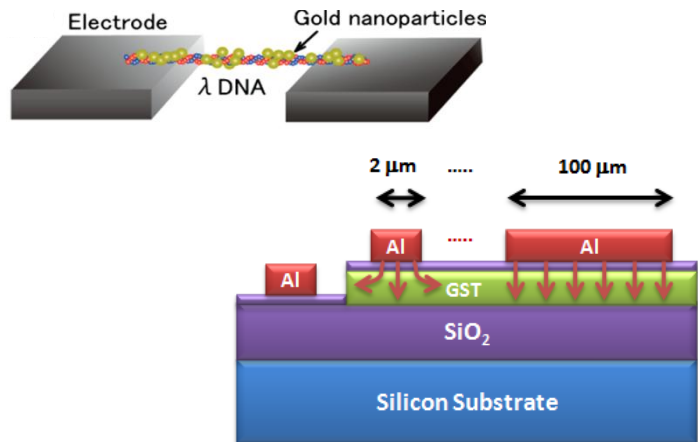
Cross-sectional IR Microscopy



Nanosecond Transient Thermoreflectance



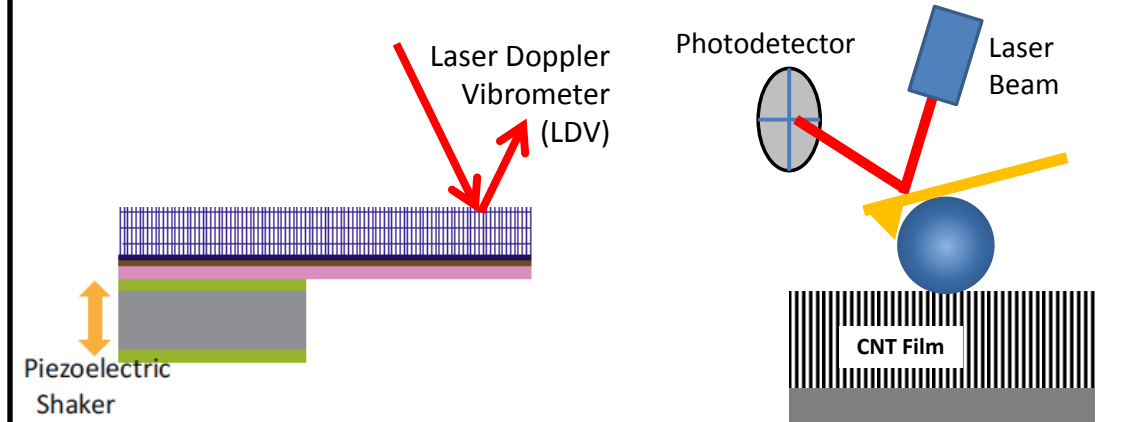
Electrothermal Characterization



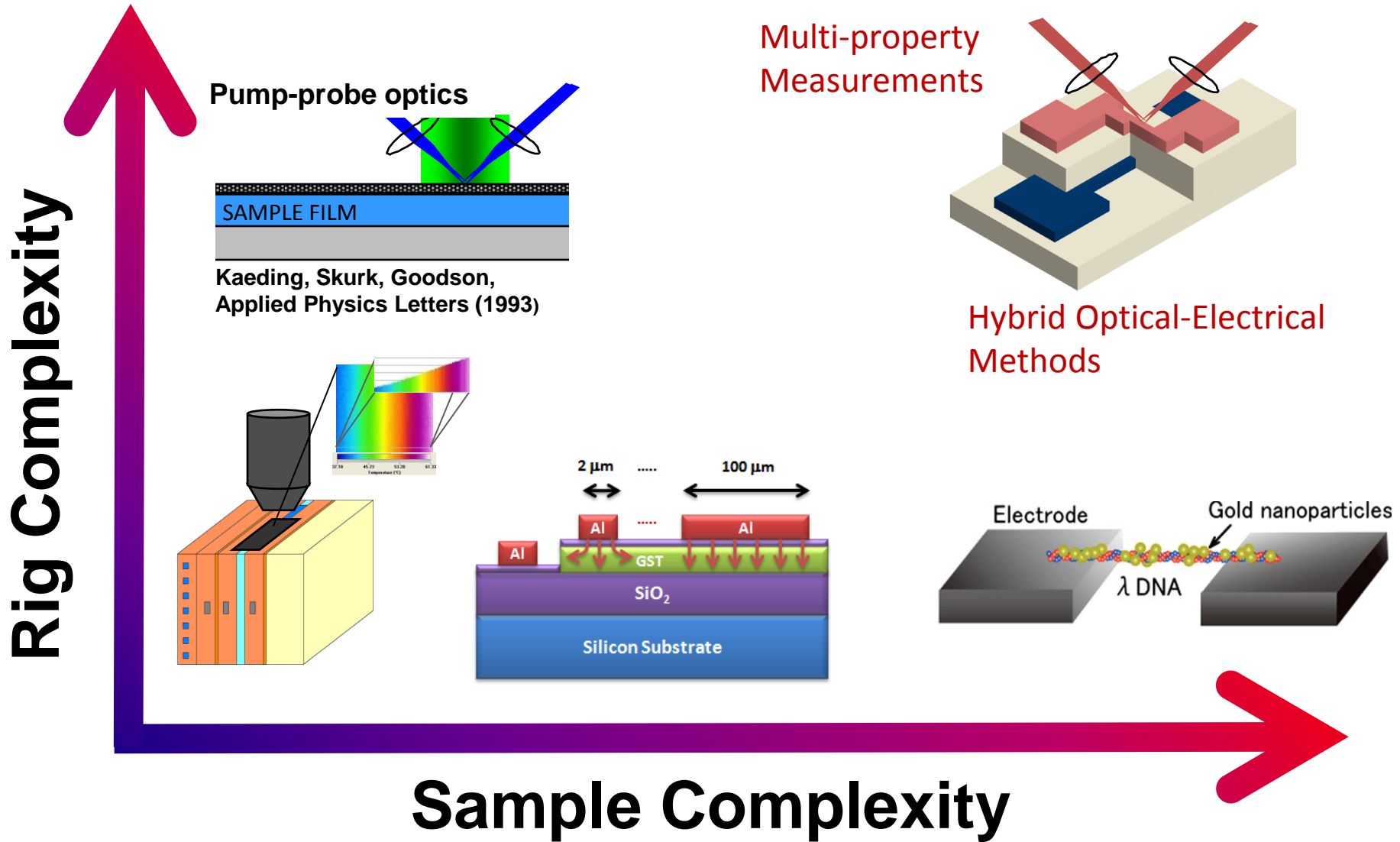
Mechanical Characterization

Microresonators (In-Plane)

Nanoindentation (Out-of-Plane)

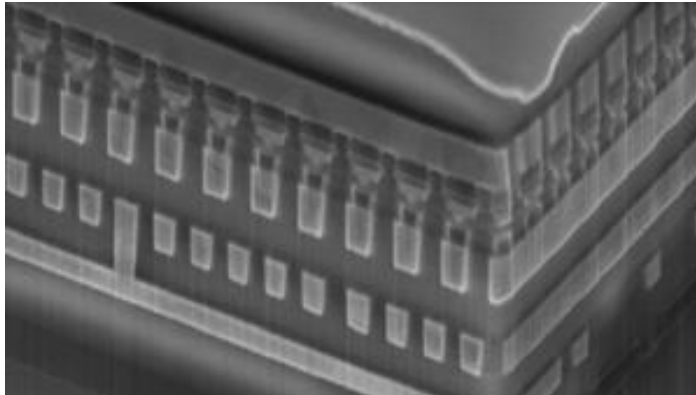


Metrology



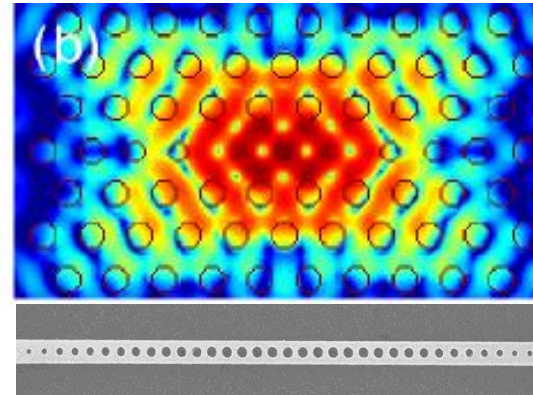
Nanodevices and Materials

Data Storage



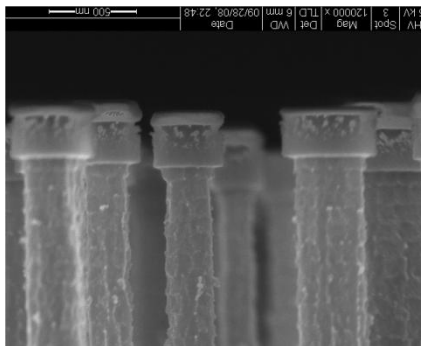
Numonyx/Intel

CMOS Lasers



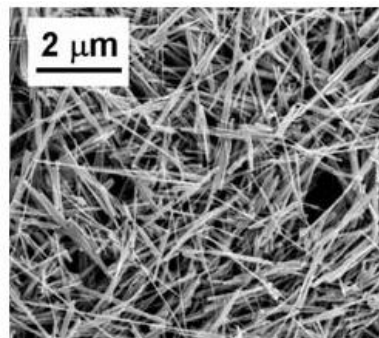
Vuckovic et al., Stanford

Thermoelectrics



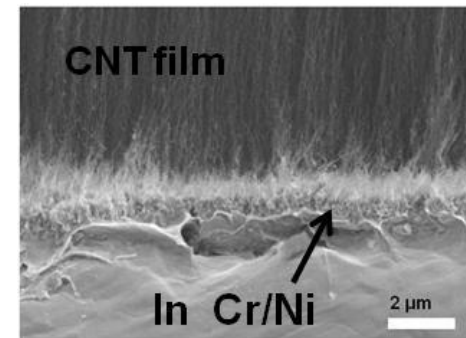
C. Xi, C-M Hsu
Cui group, Stanford

Solar Electrodes



R. Noriega and S. Phadke
Salleo group, Stanford

Thermal Interfaces



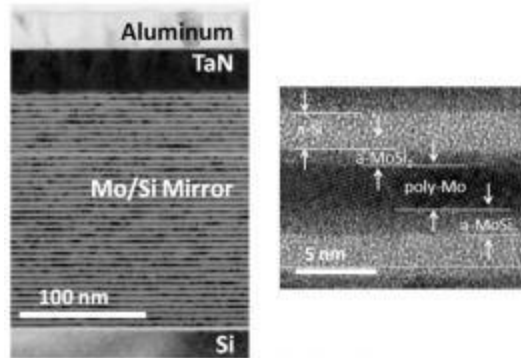
Goodson group, Stanford

Interface Physics

Zijian Li, Elah Bozorg-Grayeli, Jungwan Cho, Si Tan

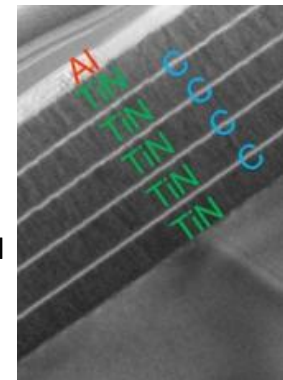
Extreme UV NanoOptics

Mo/Si Multilayer Structure



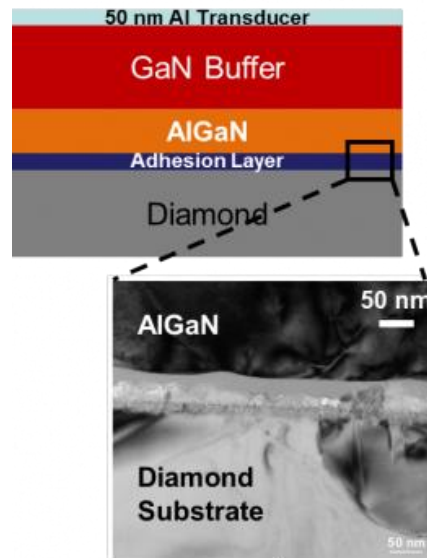
Phonon & Electron Nonequilibrium at Interfaces

Engineered multilayer interface for reducing thermal conductance in phase change memory devices

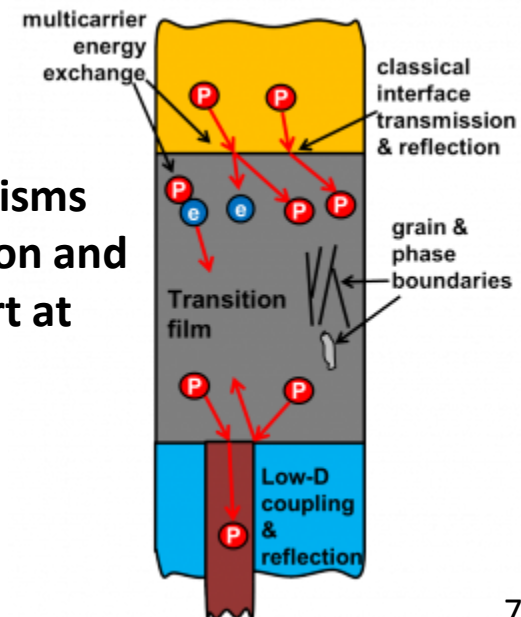


Novel Composite Substrates for Power Electronics and Photonics

GaN-diamond composite for power HEMTs (courtesy Group4 Labs)



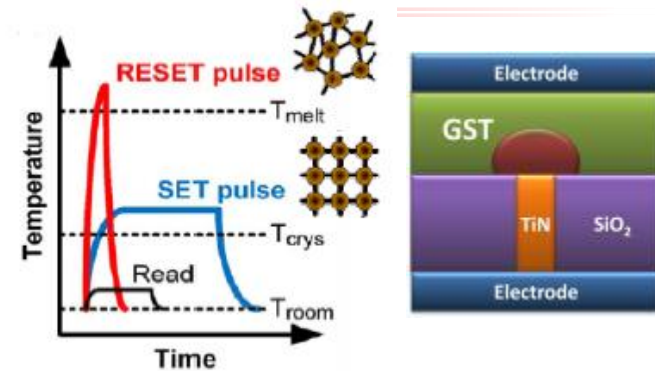
Physical mechanisms governing electron and phonon transport at interfaces



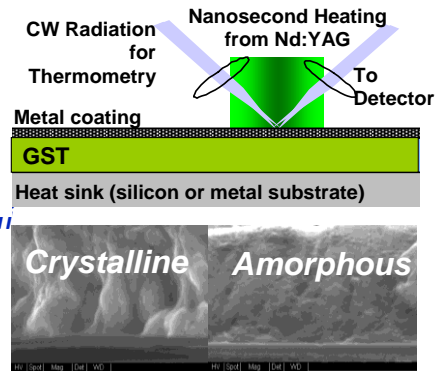
Phase Change Memory

Sponsors &
Collaborators:

Intel (D. Kau, K-W. Chang, Ilya V Karpov, G. Spadini)
NXP (F. Hurckx), Micron (John Smythe), IBM (Raoux, Krebs, et c
National Science Foundation (NSF),
Semiconductor Research Corporation (SRC)

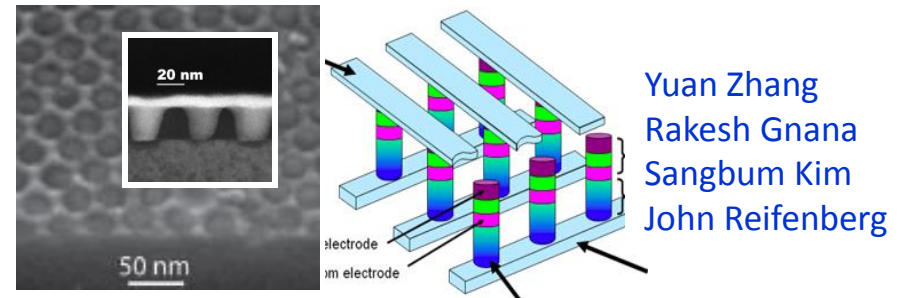


Thermal Characterization



Jaeho Lee
Zijian Li
Elah Bozorg-Grayeiri
SangBum Kim
John Reifenberg

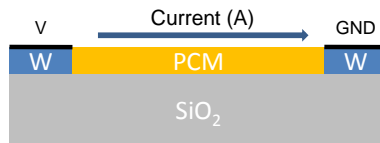
Novel Geometries, Synthesis, & Multibit



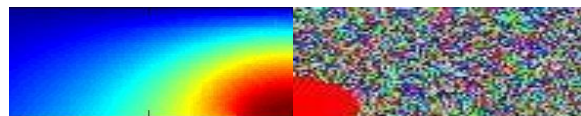
Yuan Zhang
Rakesh Gnana
Sangbum Kim
John Reifenberg

ThermoElectric Effect (Seebeck)

Jaeho Lee,
Rakesh Gnana,
Zijian Li

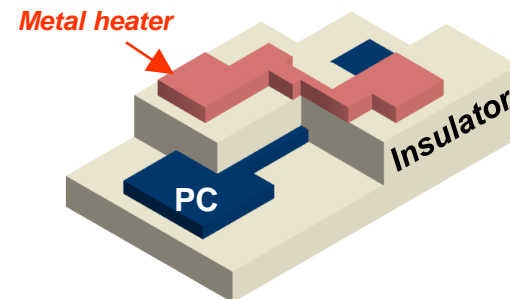


Electrothermal/Crystallization Modeling



John Reifenberg
Zijian Lee

Threshold Switching Phenomena



SangBum Kim
Rakesh Gnana,
John Reifenberg,
Jaeho Lee,
Zijian Li

MicroThermal Stage (MTS)

Key Challenges for TEs in Combustion Systems

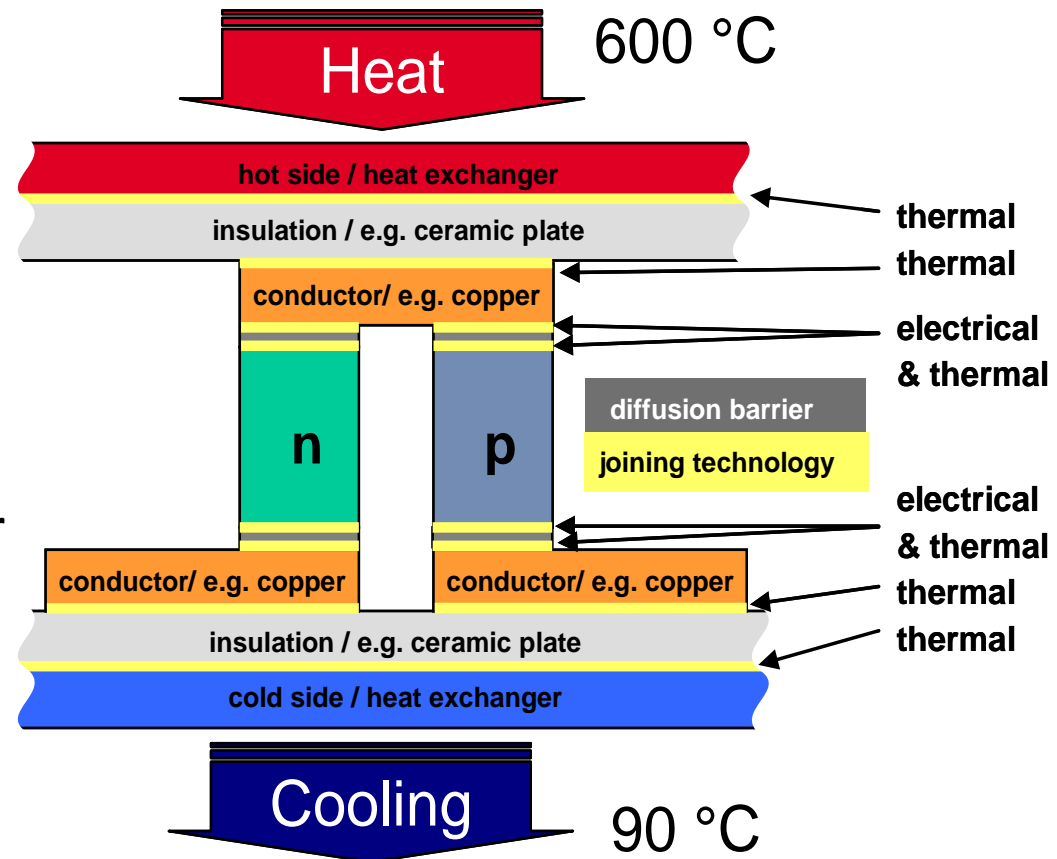
Improvements in the intrinsic ZT of TE materials are proving to be very difficult to translate into efficient, reliable power recovery systems.

Major needs include...

...Low resistance interfaces that are stable under thermal cycling.

...High-temperature TE materials that are stable and promise low-cost scaleup.

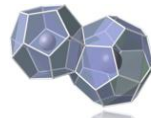
...Characterization methods that include interfaces and correlate better with system performance.



Automotive Waste Heat Recovery

Thermoelectric Modules and Electro-Thermo Interfaces

Michael Barako, Lewis Hom, Saniya Leblanc, Yuan Gao, Woosung Park, Amir Aminfar, Amy Marconnet, Dr. Mehdi Asheghi



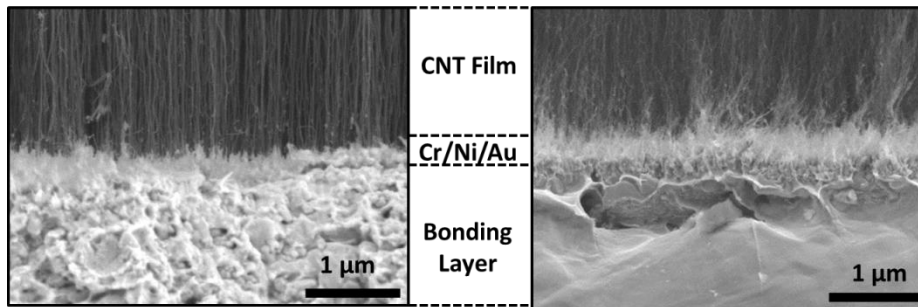
NOVEL MATERIALS LABORATORY
UNIVERSITY OF SOUTH FLORIDA



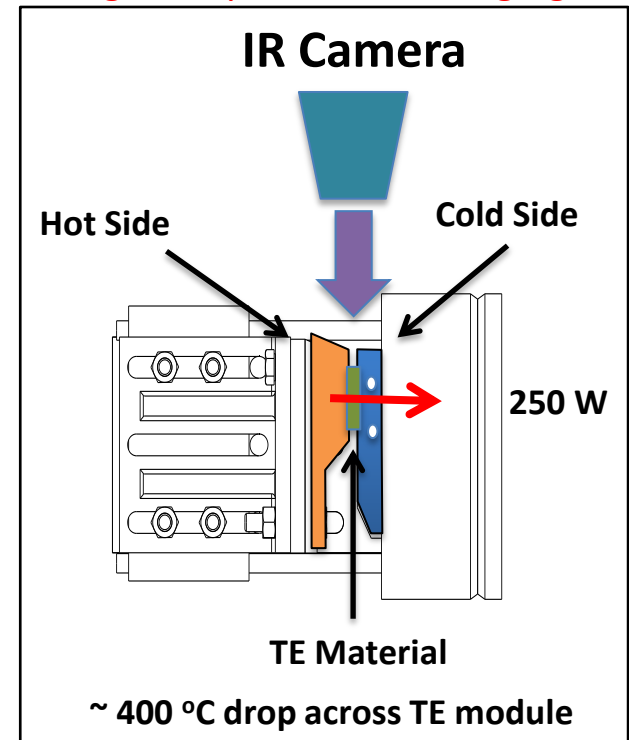
Nanofoil Bond

Solder Bonding

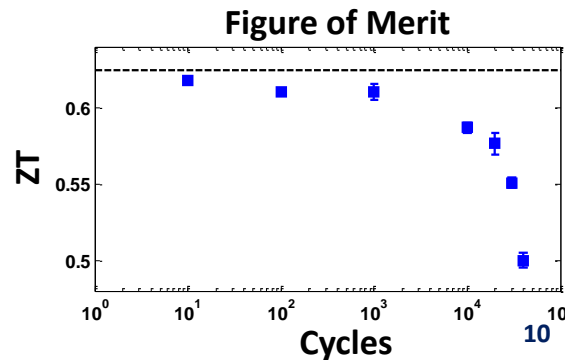
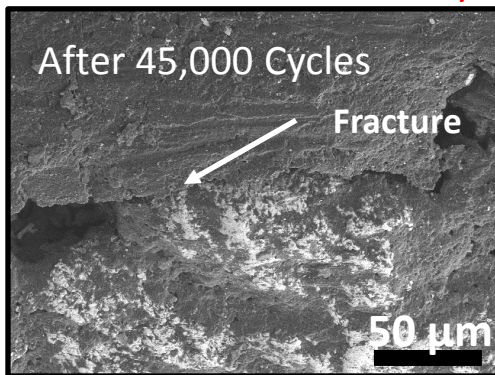
Indium Bond



High Temperature IR Imaging



Thermal Cycling of TE Modules



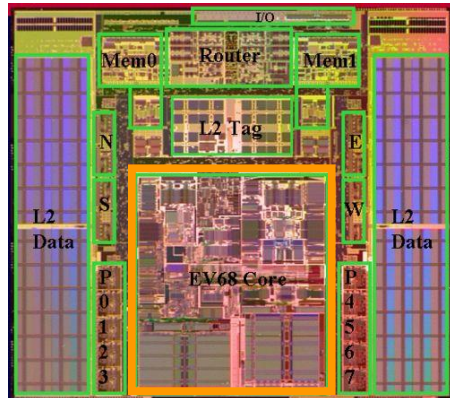
Thermal Management Challenges for Microprocessors

Importance of Hotspot Thermal Management

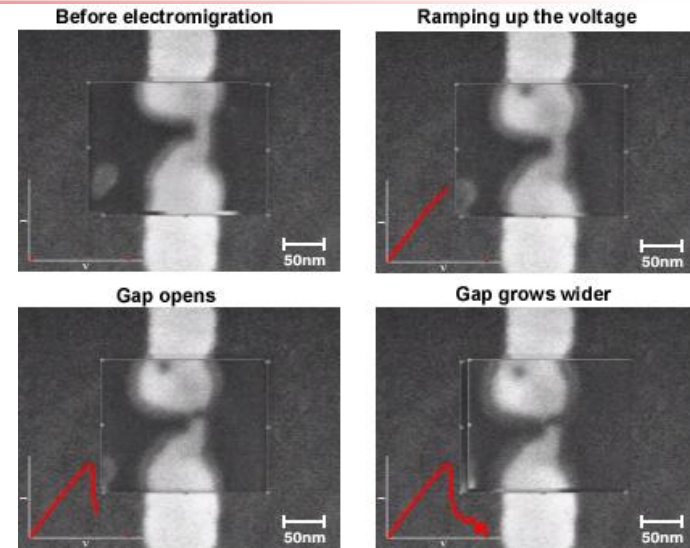
- Peak temperatures limit the reliability of interconnects
- Thermo-mechanical strains due to temperature non-uniformities can degrade packaging and interfaces

Challenges Ahead for Thermal Management

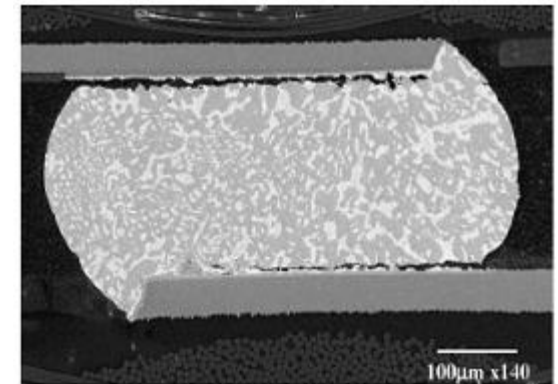
- Transistor scaling
- Increasing number of cores
- 3D integration
- Constraints of mobile applications



Adapted from: http://en.wikipedia.org/wiki/Heat_sink



Images of Electromigration Failure
Ralph Group, Cornell University



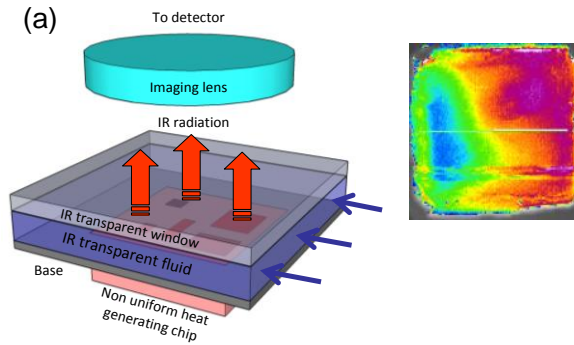
Solder joint failure due to thermomechanical stress
Ridgetop Group Inc.,

Hot Spot Detection and Thermal Management

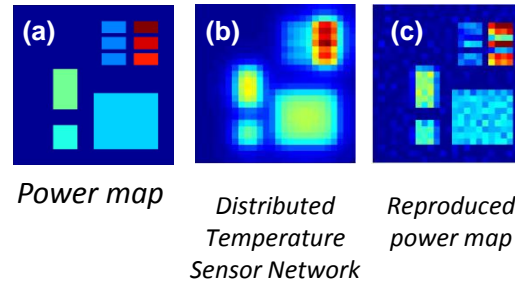
To resolve transient chip hotspots with increased accuracy and cool them with high-heat flux cooling solutions

Milnes David, Joe Miler, Lewis Hom, Dr. Mehdi Asheghi

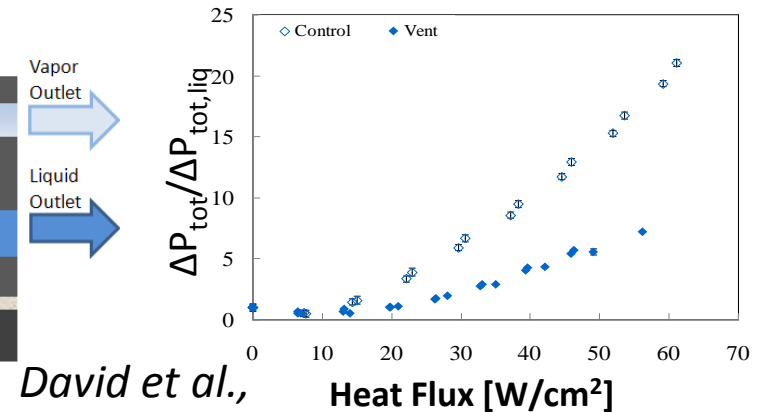
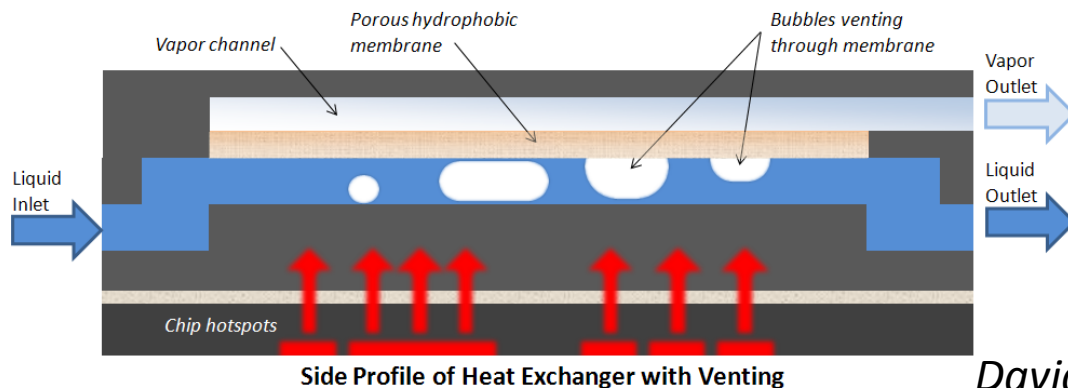
Through-Wafer Hotspot Imaging



Rapid Hotspot Prediction & Power Distribution



Vapor-Venting Microfluidic Heat Exchangers



Thermal Interface materials

3D chips: Material Requirements

Goal: Discover and characterize advanced materials containing nanoscale inclusions (particles, platelets, tubes), targeting the unique property needs of packaging applications including TSV, interposer, and 3D

TIM 1 & 2 (metal alloys, particle filled organics, aligned CNT films)

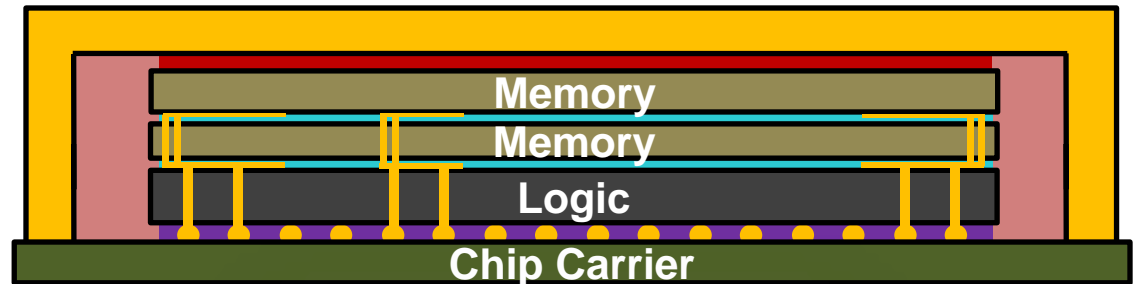
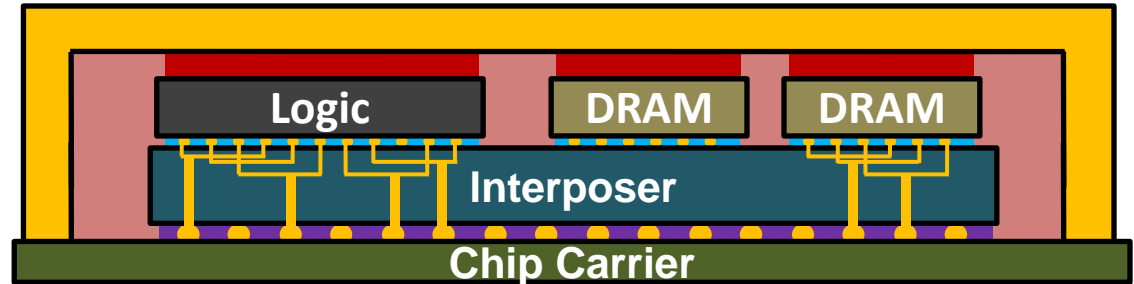
- High thermal conductivity
- Mechanical compliance

3D Chip Attachment (Adhesives, Thermal compression bonding)

- High thermal conductivity
- Electrically insulating
- Thermal cycling stability

Encapsulation

- High thermal conductivity
- Electrically insulating (on the side facing the chip)
- Mechanical compliance

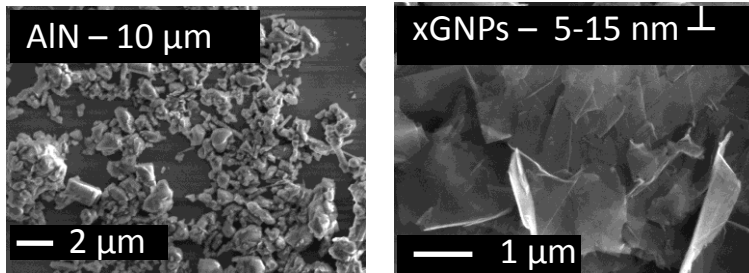


Flowable Underfill

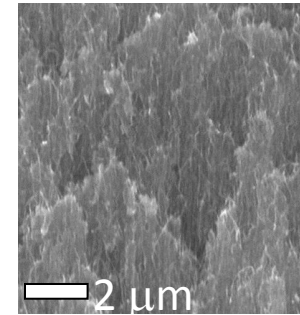
- Electrically insulating
- Mechanical stiffness
- Viscosity and capillary forces
- High thermal conductivity

Thermal Interface Materials

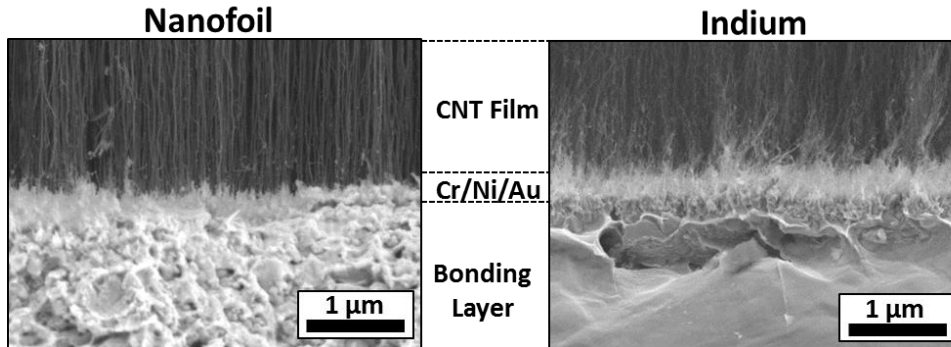
AlN-(xGNP) Exfoliated Graphene nanoplatelet composites



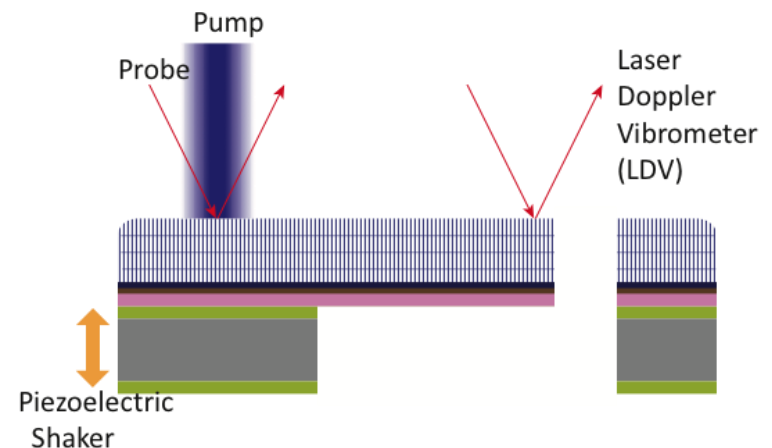
Aligned CNT Composites



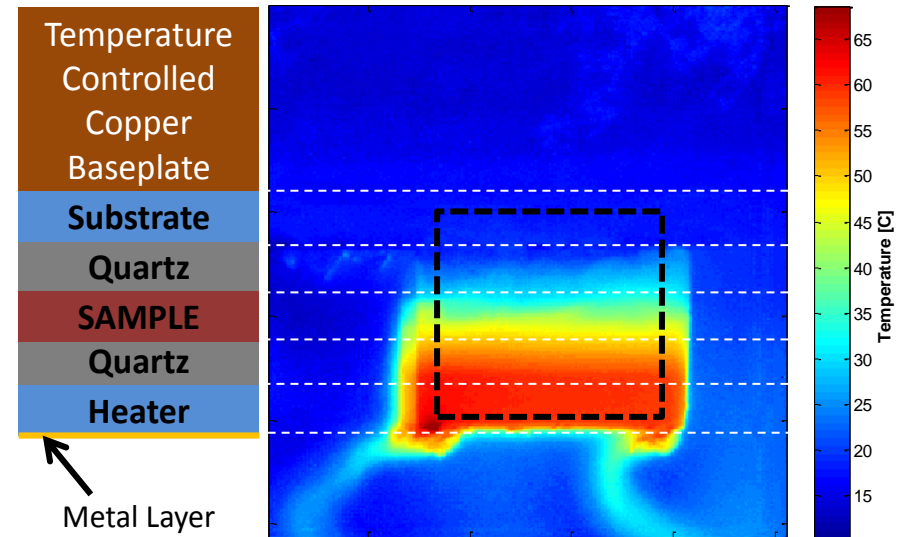
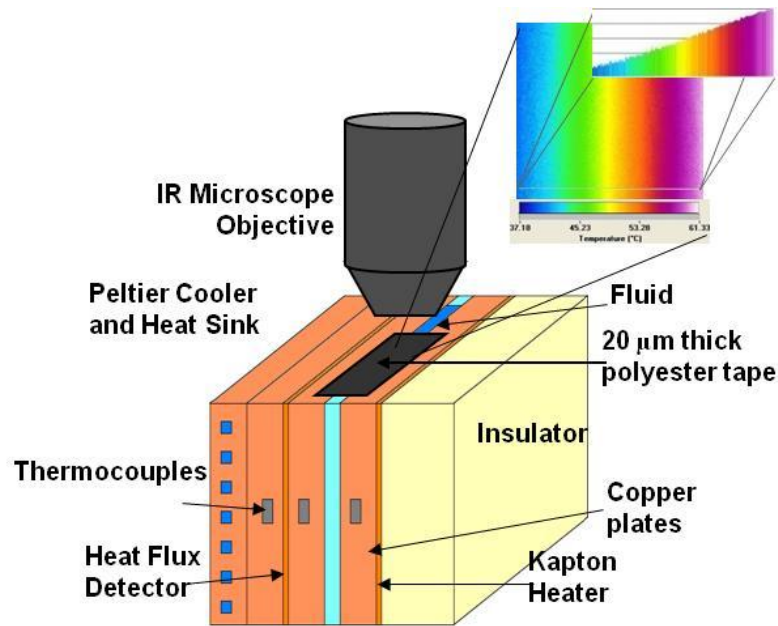
Nanotape to Replace Solder Pads



Thermal and Mechanical Characterization

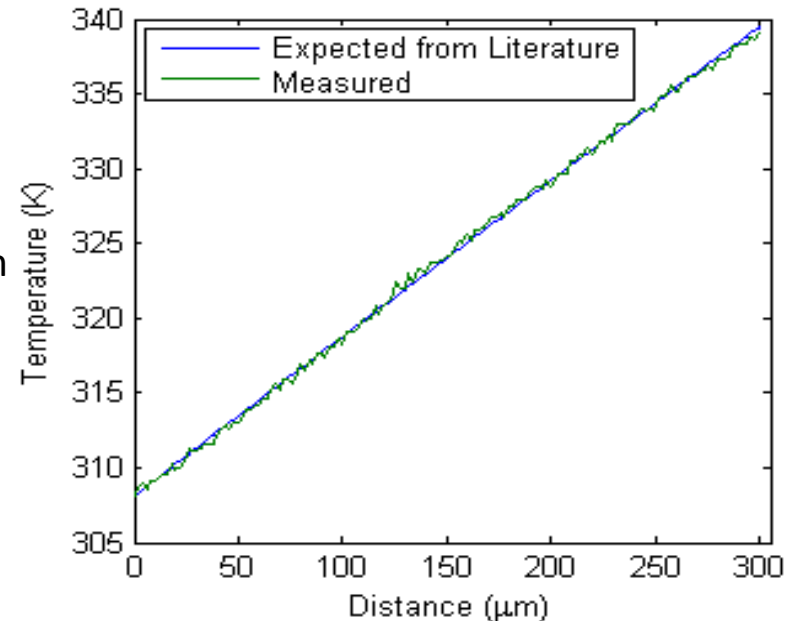


Thermal Conductivity Measurement – IR Imaging

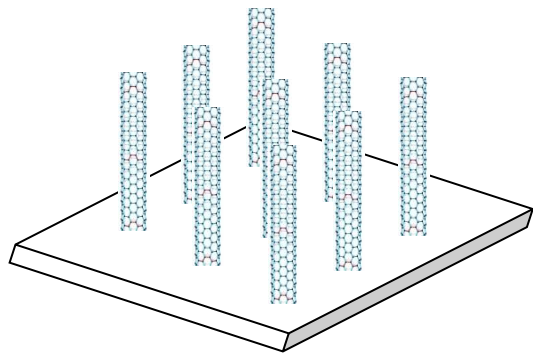


Calibration & Verification

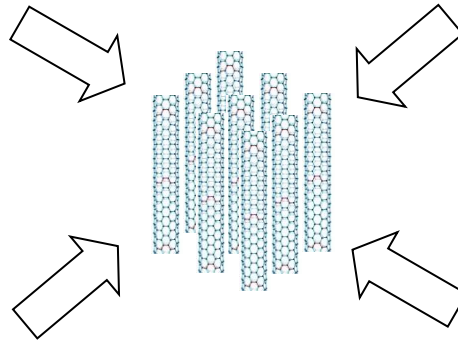
- Emitter tape defines measurement location and uniform emissivity
- Emissivity calibrated(@ 65-75 °C) using thermocouples
- Verification performed on known materials
- Dual heat flux measurement region quantify heat losses



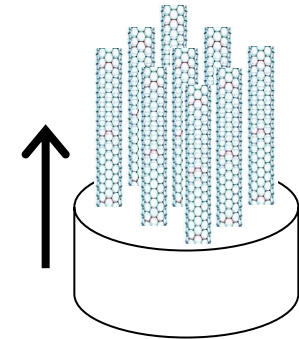
Aligned CNT Nanocomposites



Remove 1 vol.% CNT film from growth substrate

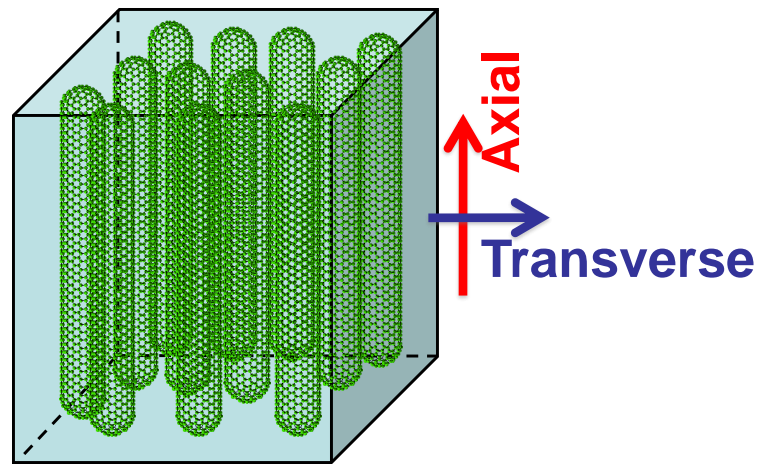
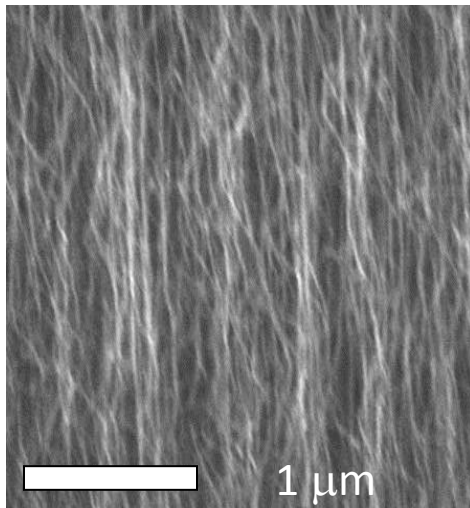


Biaxial compression to increase volume fraction



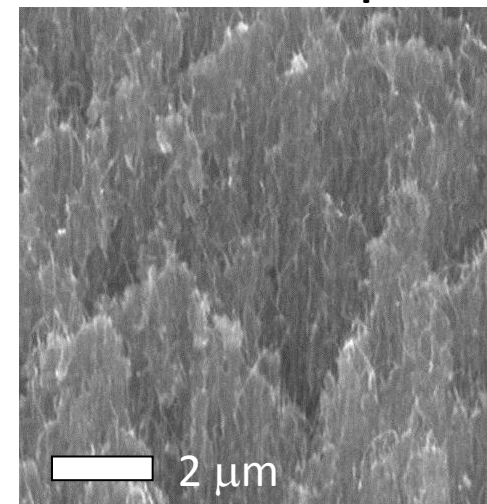
Infiltrate with epoxy (RTM-6)

1 vol.% CNT film

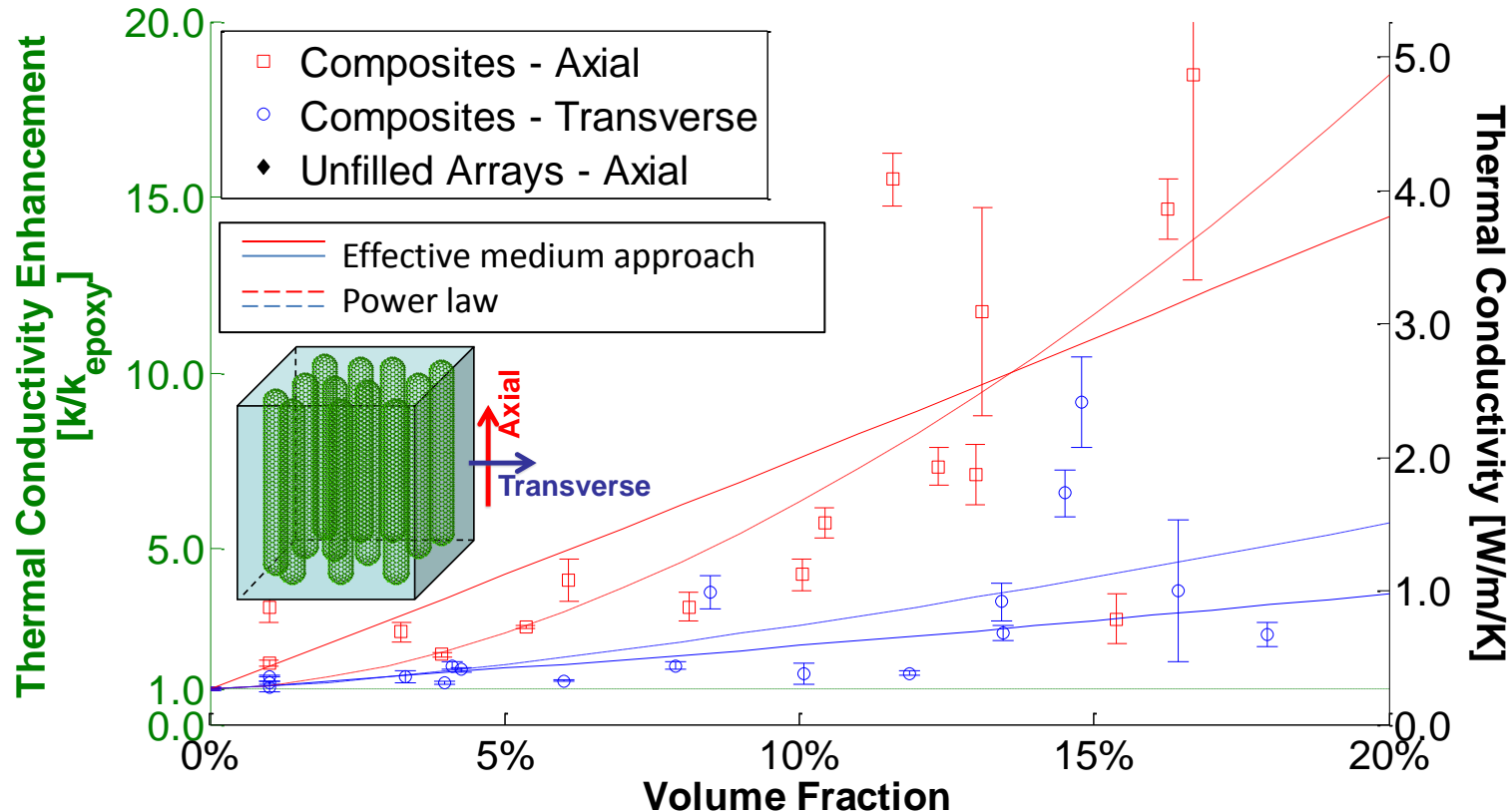


Marconnet et al, *ACS Nano* (2011)

1 vol.% CNT Composite



Thermal Conductivity of Aligned CNT Nanocomposites

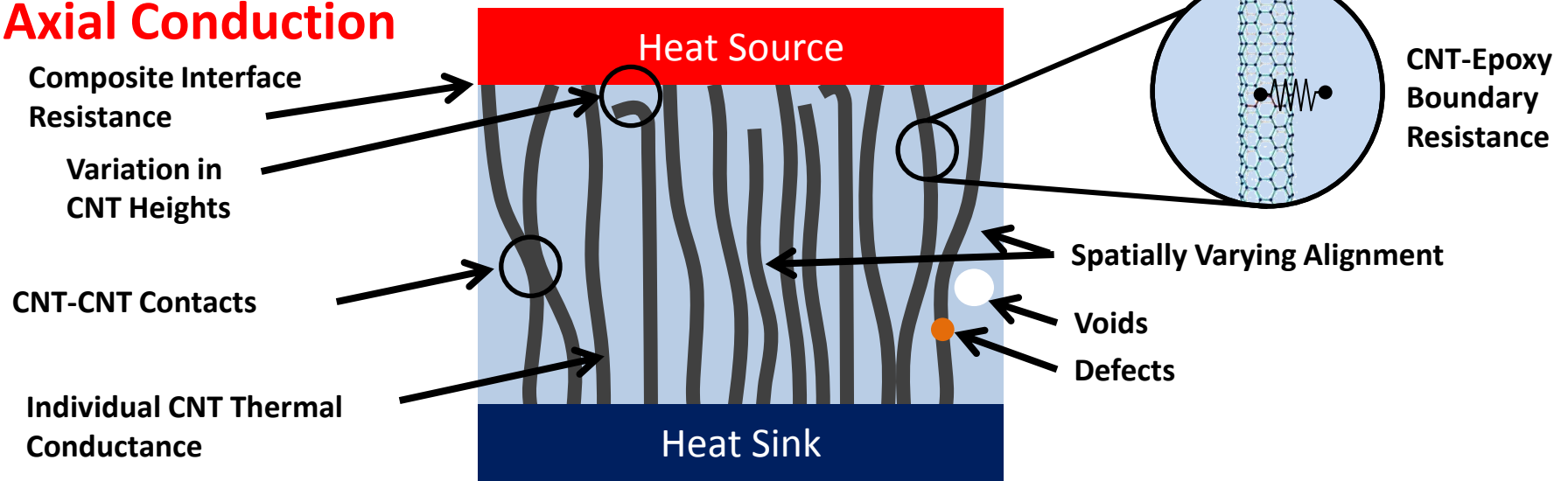


(Surfaces polished to $\sim 3\text{nm}$ roughness and coated with 200 nm of Pt to ensure nearly identical contact conditions for all samples and improves contact between composite and reference layers)

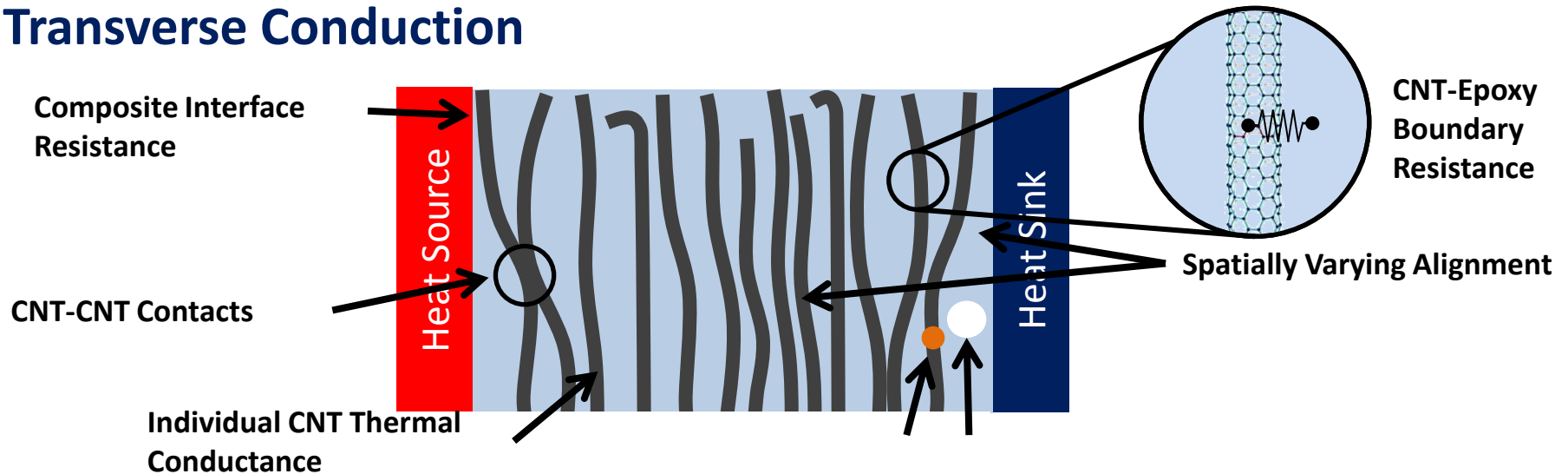
- **Non-linear increase at higher volume fraction suggests that CNT-CNT and CNT-polymer interactions are important to the thermal transport**
- **CNT's contribute at a rate of about 10 W/m/K per CNT at low volume fractions, much lower than expected.**

Aligned CNT Nanocomposites

Axial Conduction



Transverse Conduction



Nanotape to Replace Solder Pads

EE Times News & Analysis

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News & Analysis

Nanotape could make solder pads obsolete

R. Colin Johnson

1/24/2011 12:01 AM EST

PORTLAND, Ore.—Solder pads could soon be made obsolete by a new nanotape material created by the Semiconductor Research Corporation and Stanford University.

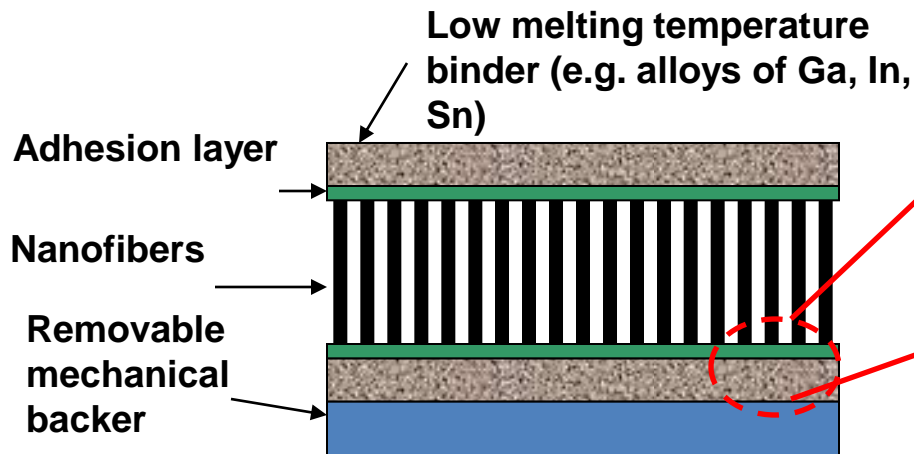
By sandwiching thermally conductive carbon nanotubes between thin r

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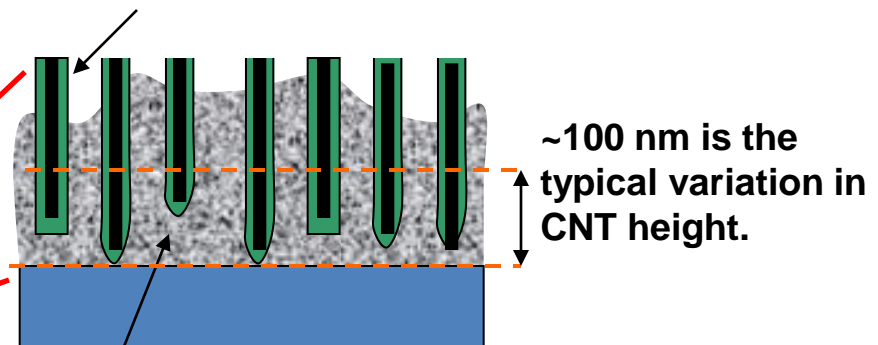
SRC Patent: Hu, Jiang, Goodson, US Patent 7,504,453, issued 2009

SRC Patent: Panzer, Goodson, et al., 2009/0068387 (pending)

Panzer, Maruyama, Goodson et al., Nanoletters (2010)
Hu, Fisher, Goodson et al., J. Heat Transfer (2006)

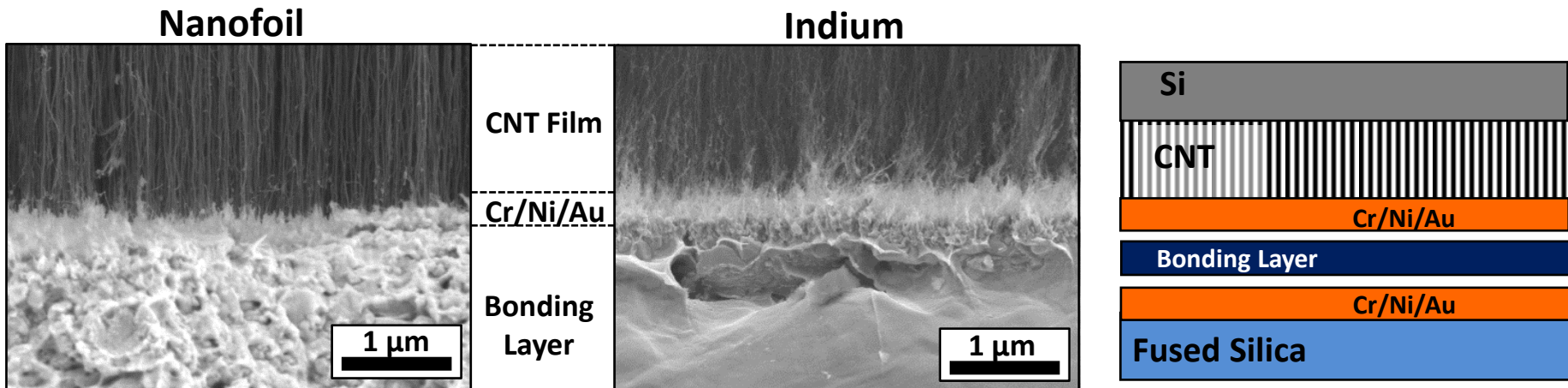


Adhesion layer wets nanotubes and promotes adhesion of binder (Pd, Pt, or Ti).

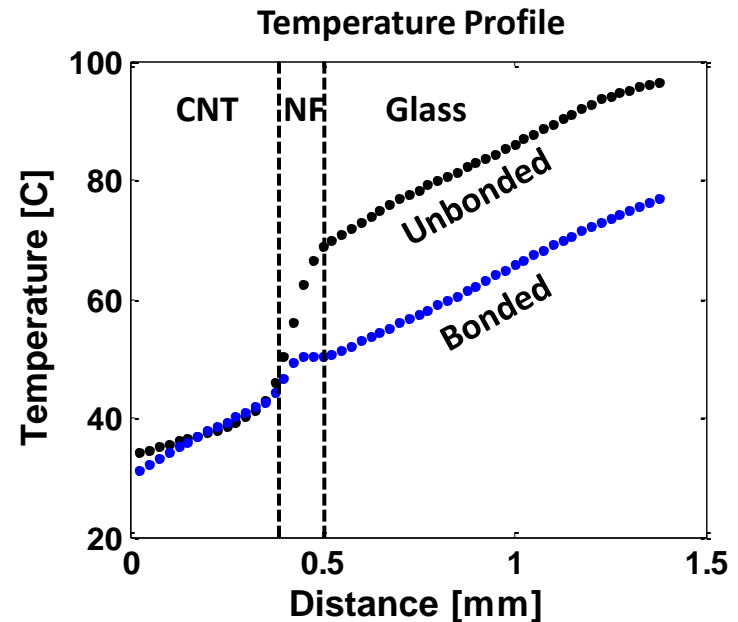


Upon heating, the low melting binder conforms to CNT and substrate topography.

Bonded CNT Thermal Properties



For constant q'' , the interfacial temperature drop is reduced by an order of magnitude through solder bonding

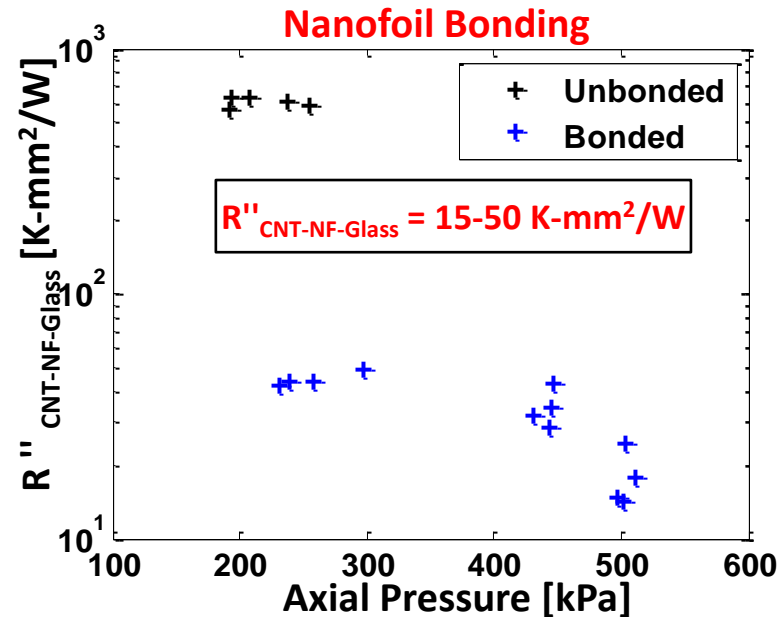
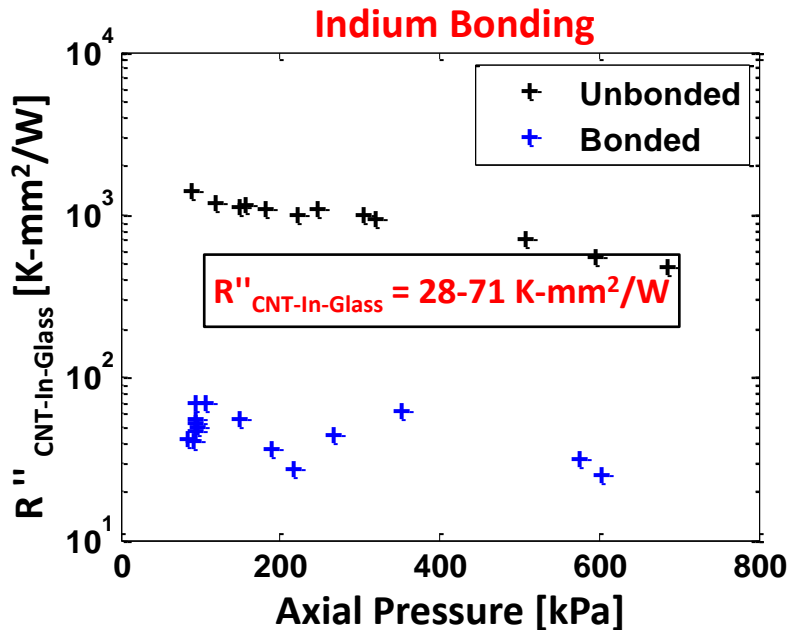
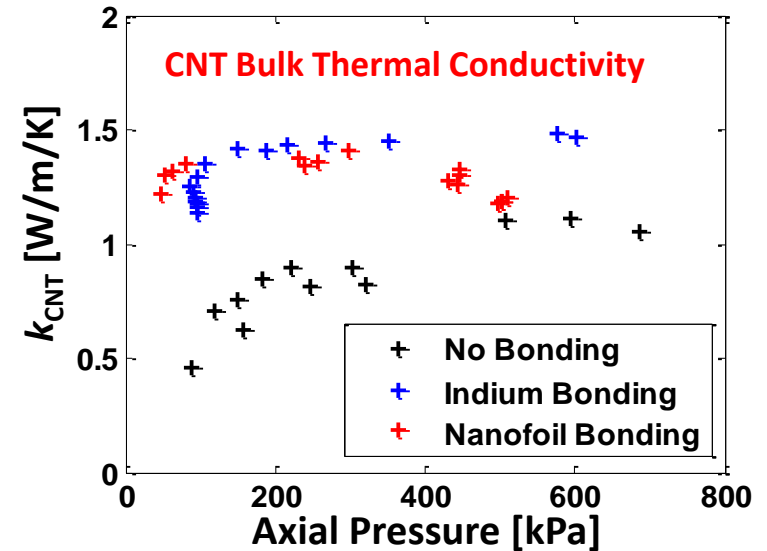


Barako et al, IThERM 2012

Bonded CNT Thermal Properties

- Intrinsic Thermal Conductivity increases due to improved engagement of CNTs
- Thermal boundary resistance decreases significantly

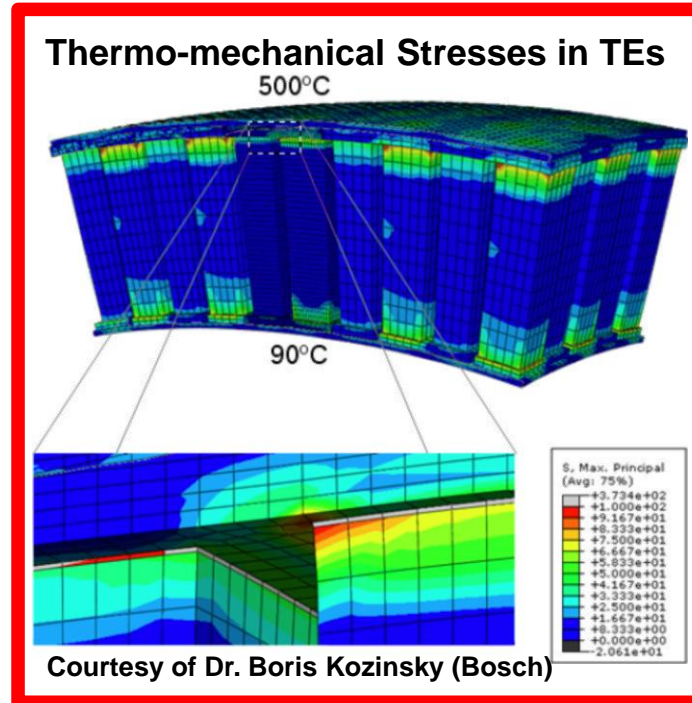
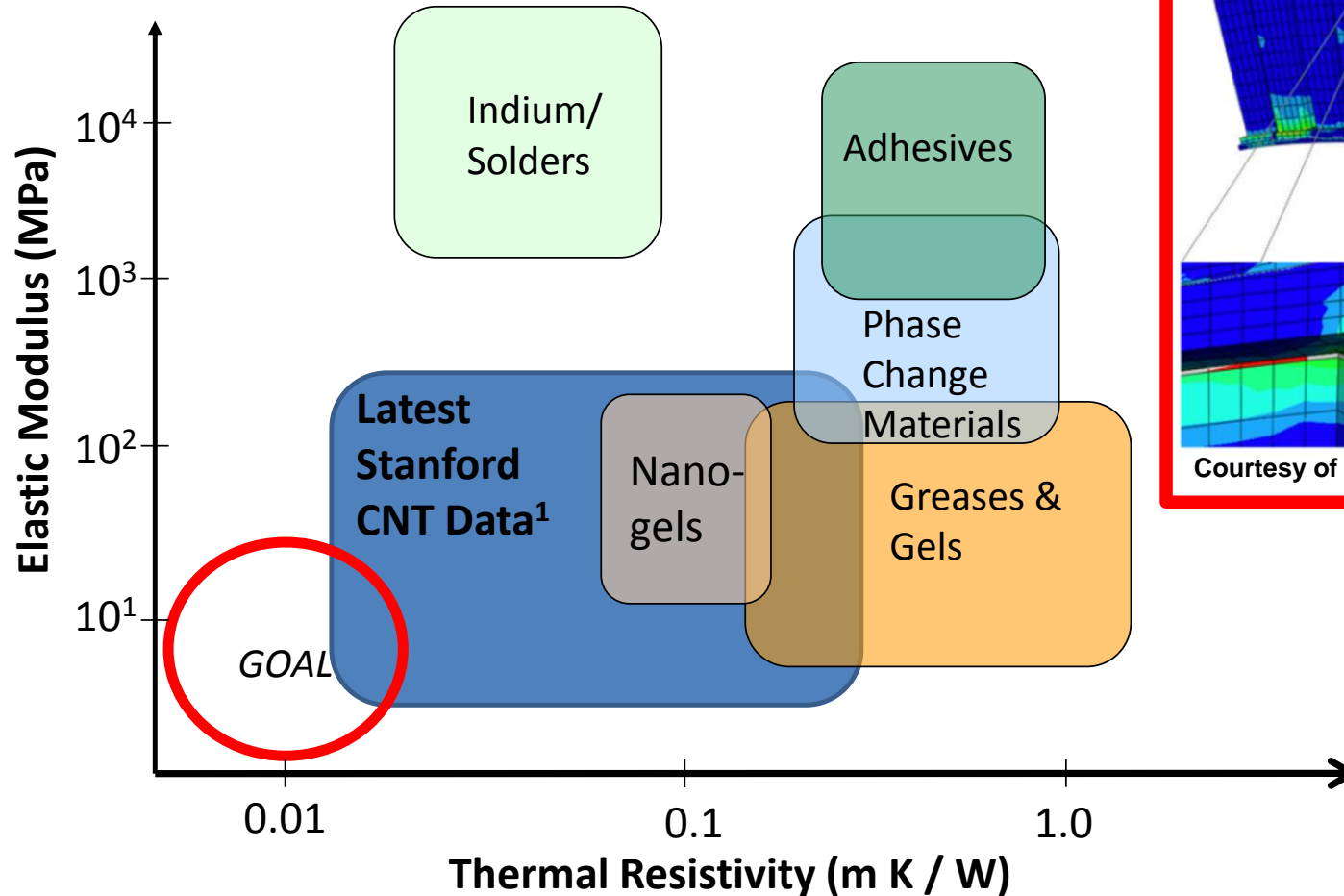
Barako et al, IThERM 2012



Thermal Interface Materials

GOAL: Thermal Conductivity + Mechanical Flexibility

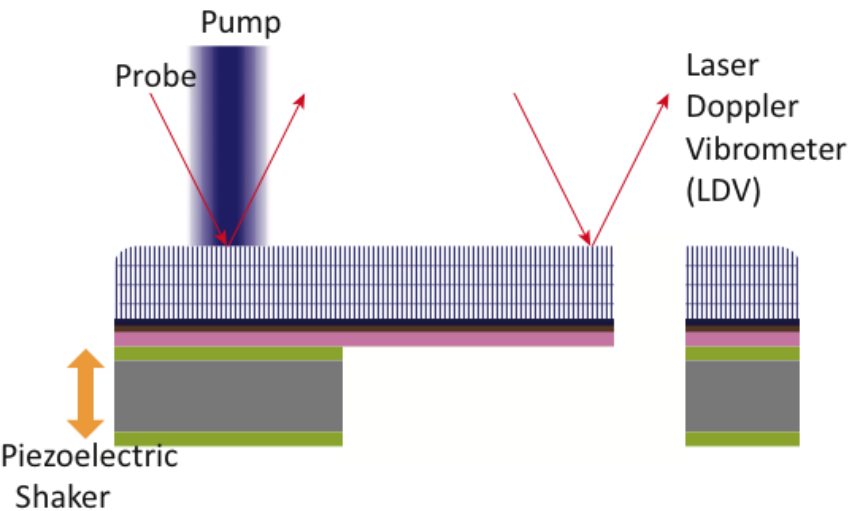
Implication: Higher package form factor



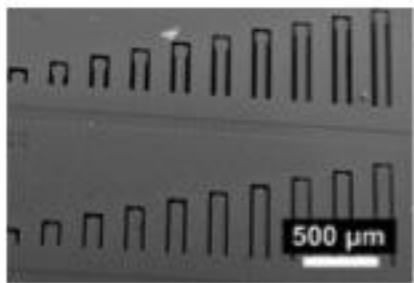
Mechanical Properties of CNT Films

New Technique: Mechanical Resonators

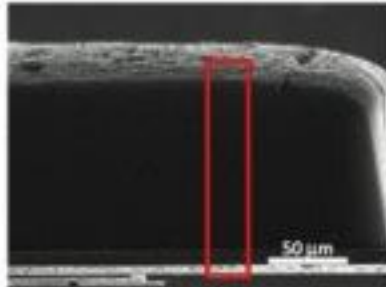
Thermal and Mechanical Characterization



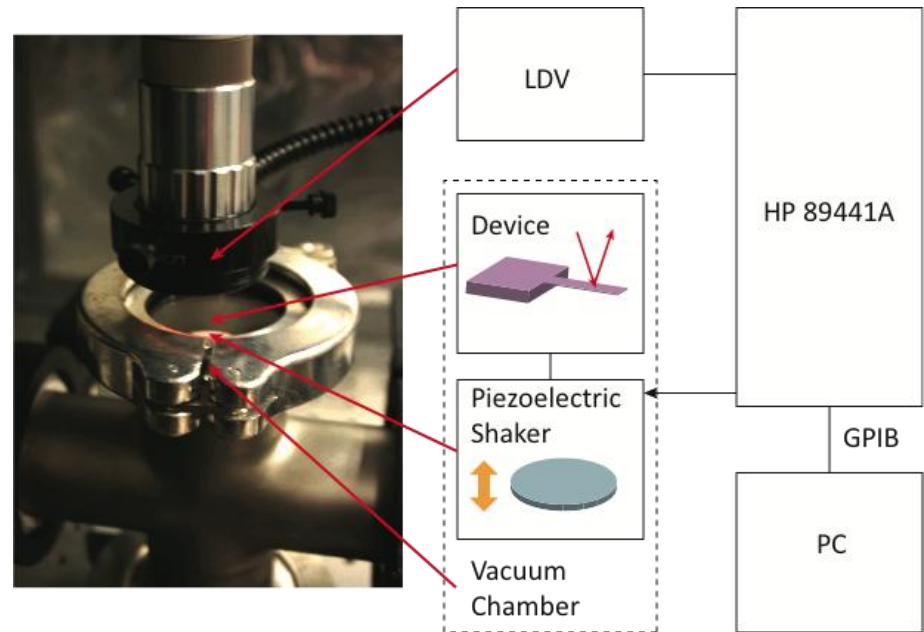
Resonator length and shape variation



CNT on a Cantilever



Experimental Setup



- LDV (laser Doppler velocimetry) experimental setup : resonant frequency of various thickness films.
- Resonant frequency shift : mechanical modulus
- Ring-down and fitting measurements : quality factors

Experimental Method and Data Interpretation

Euler-Bernoulli differential equation for multi-layer beam

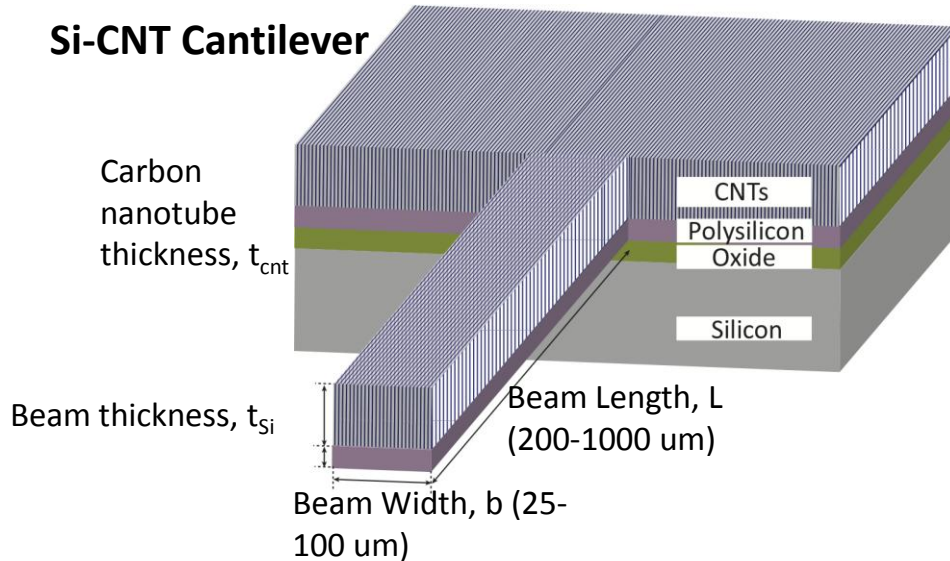
$$\overline{\rho A} \frac{\partial^2 w}{dt^2} + \overline{EI} \frac{\partial^4 w}{\partial x^4} = 0 \quad \overline{\rho A} = \sum_i \rho_i A_i \quad \overline{EI} = \sum_i E_i I_i$$

Transformed section method

$$\frac{\Delta w_n}{w_{n,o}} = \sqrt{\frac{E_{Si} I_{Si} + E_{cnt} I_{cnt}}{\rho_{Si} A_{Si} + \rho_{cnt} A_{cnt}}} \sqrt{\frac{\rho_{Si} A_{Si}}{E_{Si} I_{Si,o}}} - 1$$

$$E_{CNT} = \frac{E_{Si}}{I_{CNT}} \cdot \left(1 + \frac{\rho_{CNT} A_{CNT}}{\rho_{Si} A_{Si}} \right) \cdot \left(1 + \left(\frac{\Delta w_n}{w_{n,Si,0}} \right)^2 \right) I_{Si,0} - I_{Si}$$

Si-CNT Cantilever



Polysilicon deposition



Resonator outline etching



Resonator etching



Oxide layer removal



Catalyst deposition

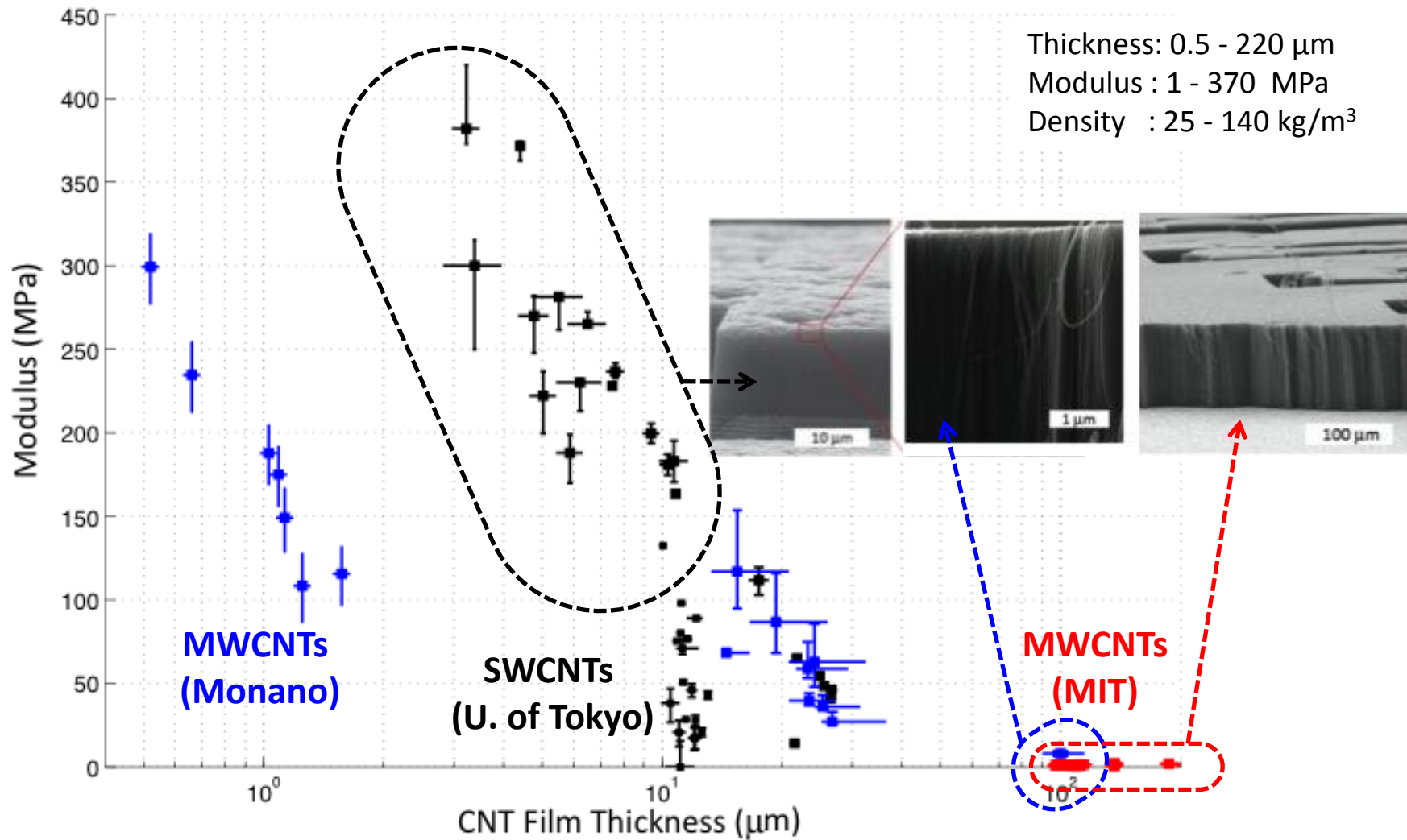


Carbon Nanotube Growth



Won et al, *Carbon* (2011)

Mechanical Behavior of CNT Films

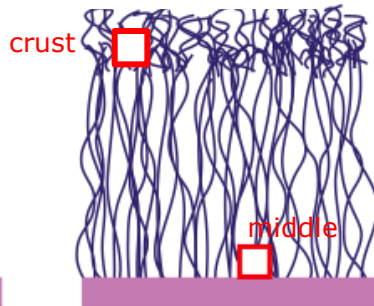


Mechanical Behavior of Nonhomogeneous CNT Films

Growth Stages

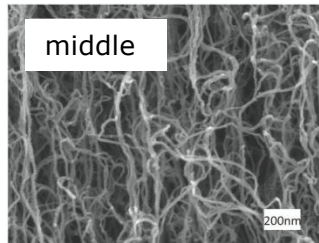
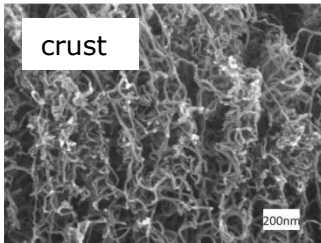
Stage 1

Stage 2



Self-organization

Vertical-growth



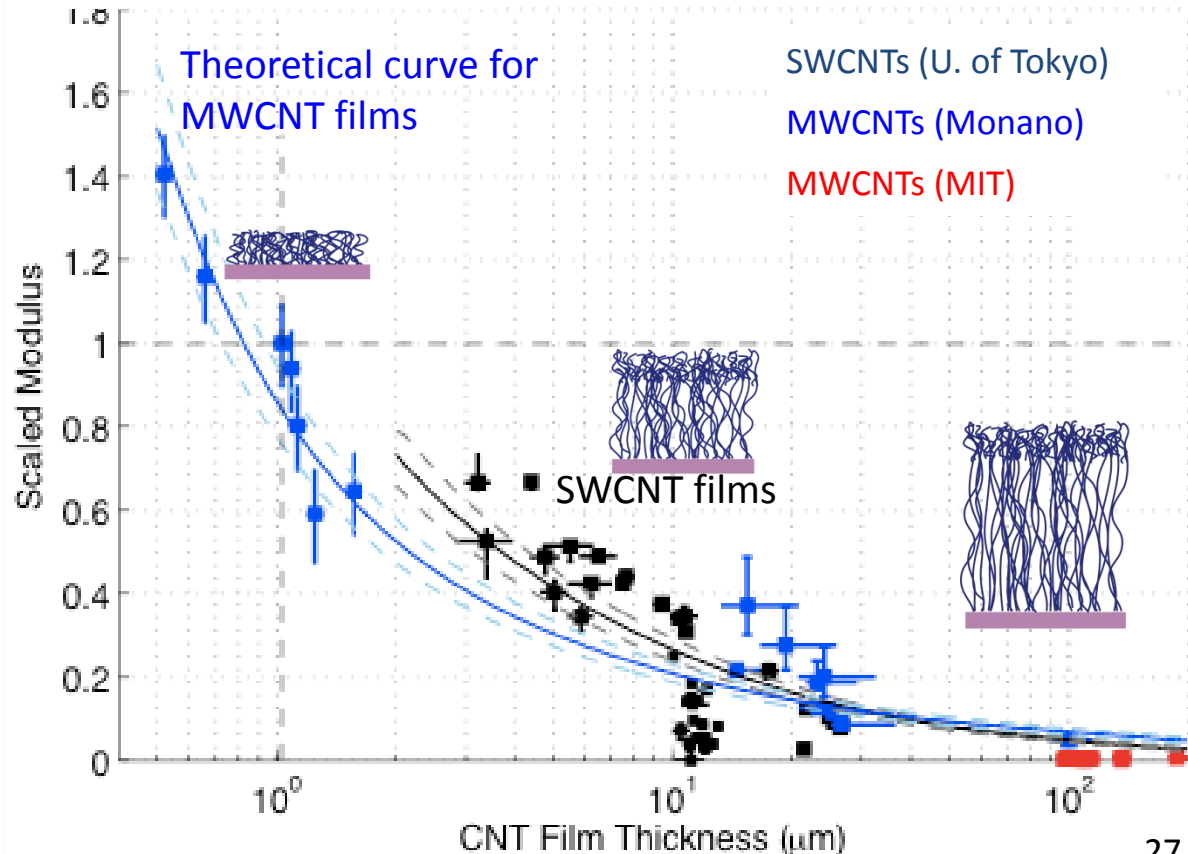
- Interweaving of a thin layer of entangled and randomly oriented nanotubes
- Vertical-aligned growth
- Density decay

Three-layer Analysis

Two-layer analysis → Three-layer analysis

$$\frac{\Delta W_n}{w_{n,Si,0}} = \sqrt{\frac{E_{Si}I_{Si,1} + E_{Middle}I_{Middle} + E_{Top}I_{Top}}{\rho_{Si}A_{Si} + \rho_{Middle}A_{Middle} + \rho_{Top}A_{Top}}} \cdot \sqrt{\frac{\rho_{Si}A_{Si}}{E_{Si}I_{Si,0}}} - 1$$

Dimensionless Effective Modulus : Moduli are scaled by reference sample and volume fraction



Conclusions - Materials for Thermal Management

- Development of novel thermal interface materials is crucial for 3D circuits performance
- Nano tape is a promising replacement to solder pads
- Measurements of aligned CNT films and composites showed thermal conductivity and elastic modulus comparable to or better than commercial TIMs
- Thermal conductivity data of AlN-xGNP nanocomposites showed promising trends and are potential candidates for underfill materials

Questions & Comments

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